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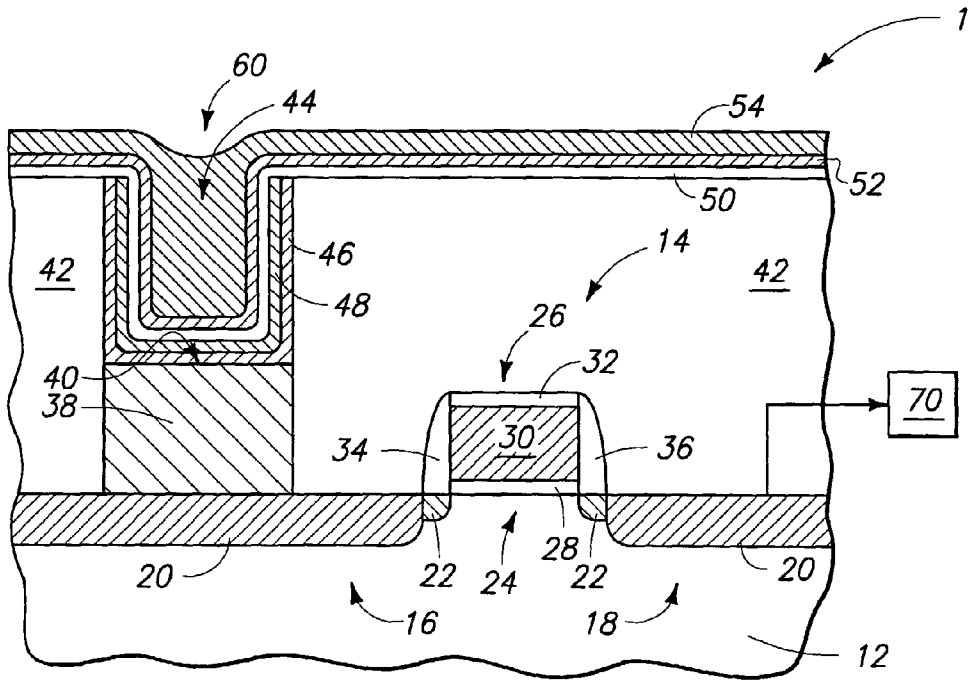
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(54) Title: CAPACITOR CONSTRUCTIONS, AND THEIR METHODS OF FORMING



(57) Abstract: The invention includes methods in which metal oxide dielectric materials (50) are deposited over barrier layers (48). The barrier layers can comprise compositions of metal and one or more of carbon, boron and nitrogen, and the metal oxide of the dielectric material can comprise the same metal as the barrier layer. The dielectric material/barrier layer constructions can be incorporated into capacitors. The capacitors can be used in, for example, DRAM cells, which in turn can be used in electronic systems.

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